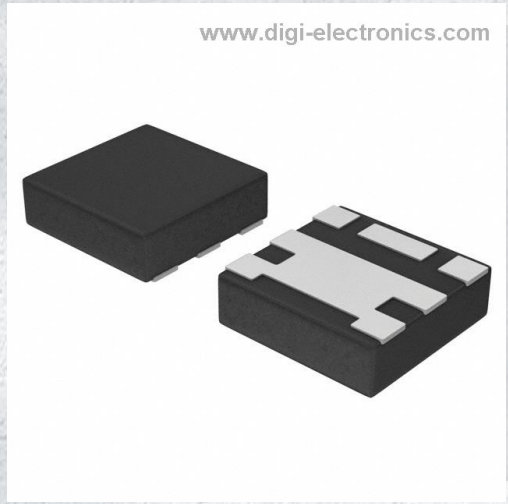
DMN6070SFCL-7 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	DMN6070SFCL-7-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DMN6070SFCL-7
Description	MOSFET N-CH 60V 3A X1-DFN1616-6
Detailed Description	N-Channel 60 V 3A (Ta) 600mW (Ta) Surface Mount X1-DFN1616-6 (Type E)

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMN6070SFCL-7	Diodes Incorporated
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
60 V	3A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4V, 10V	85mOhm @ 1.5A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
3V @ 250µA	12.3 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	606 pF @ 20 V
FET Feature:	Power Dissipation (Max):
-	600mW (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
X1-DFN1616-6 (Type E)	6-PowerUFDFN
Base Product Number:	
DMN6070	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	

Lead-free Green

DMN6070SFCL

60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_A = +25°C
60V	85 mΩ @ V_{GS} = 10V	3.0A
	120 mΩ @ V_{GS} = 4V	2.5A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- Analog Switch

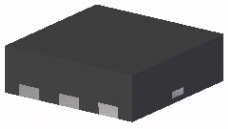
Features and Benefits

- Typical off board profile of 0.5mm - ideally suited for thin applications
- Low $R_{DS(ON)}$ – minimizes conduction losses
- PCB footprint of 2.56mm^2
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

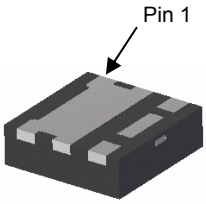
Mechanical Data

- Case: X1-DFN1616-6 Type E
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Lead Free Plating (NiPdAu Finish over Copper leadframe)
- Terminals: Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.04 grams (approximate)

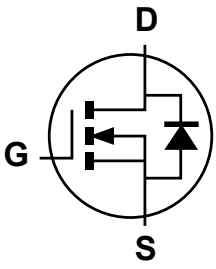
X1-DFN1616-6
Type E



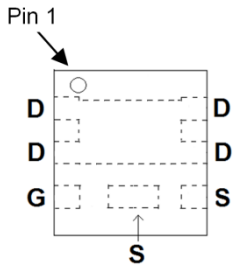
Top View



Bottom View



Device Symbol



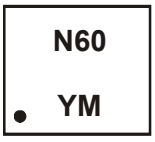
Top View
Pin-Out

Ordering Information (Note 4)

Product	Reel size (inches)	Tape Width (mm)	Quantity per Reel
DMN6070SFCL-7	7	8	3,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



N60 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	3.0 2.5	A
Pulsed Drain Current (10µs pulse, Duty cycle = 1%)			I_{DM}	10	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P_D	0.6	W
	(Note 6)		1.8	W
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	200	°C/W
	(Note 6)		67	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics N-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1.0	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±16V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	67	85	mΩ	V_{GS} = 10V, I_D = 1.5A
			74	120		V_{GS} = 4V, I_D = 0.5A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	2.6	—	S	V_{DS} = 5V, I_D = 1.5A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 3A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	606	—	pF	V_{DS} = 20V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	32.6	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	24.6	—	pF	
Gate Resistance	R_g	—	1.5	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} =10V)	Q_g	—	12.3	—	nC	V_{DS} = 30V, I_D = 3A
Total Gate Charge (V_{GS} =4.5V)	Q_g	—	5.6	—	nC	
Gate-Source Charge	Q_{gs}	—	1.7	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.9	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	3.5	—	ns	V_{GS} = 10V, V_{DS} = 30V, R_G = 20Ω, R_L = 50Ω
Turn-On Rise Time	t_r	—	4.1	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	35	—	ns	
Turn-Off Fall Time	t_f	—	11	—	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

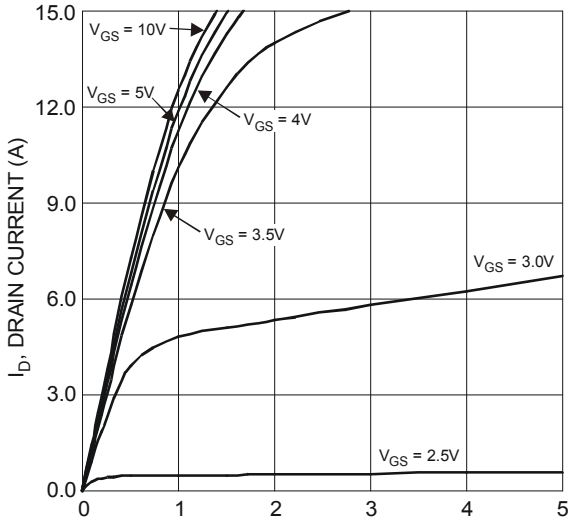


Figure 1 Typical Output Characteristics

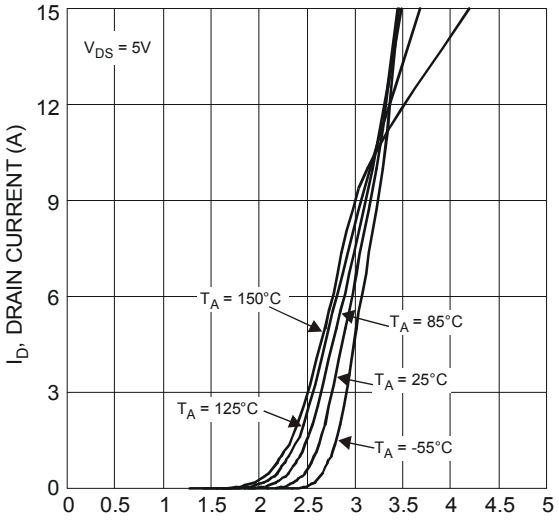


Figure 2 Typical Transfer Characteristics

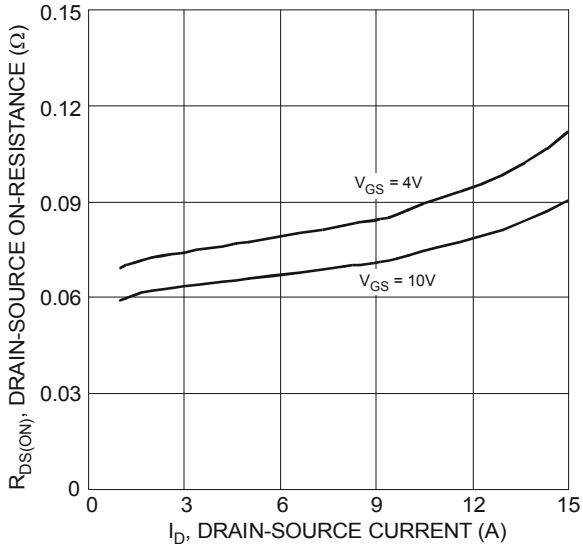


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

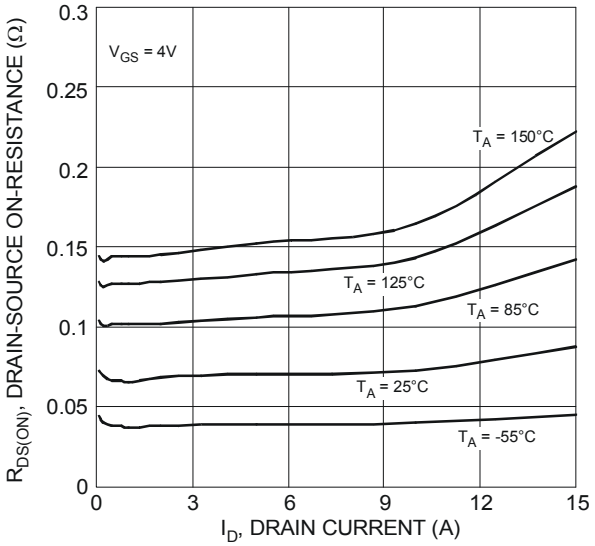


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

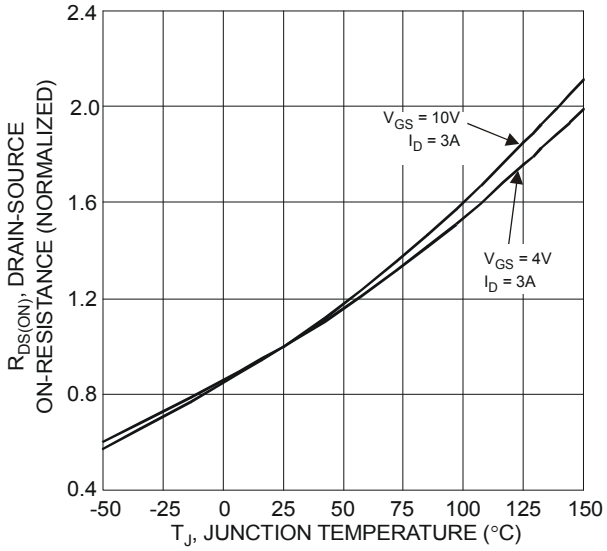


Figure 5 On-Resistance Variation with Temperature

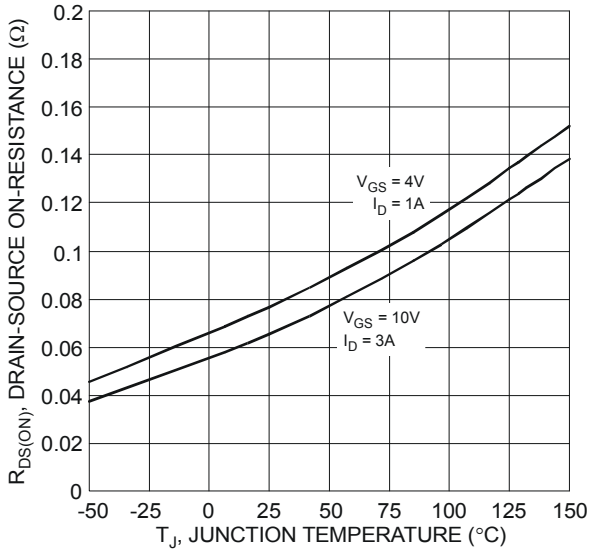


Figure 6 On-Resistance Variation with Temperature

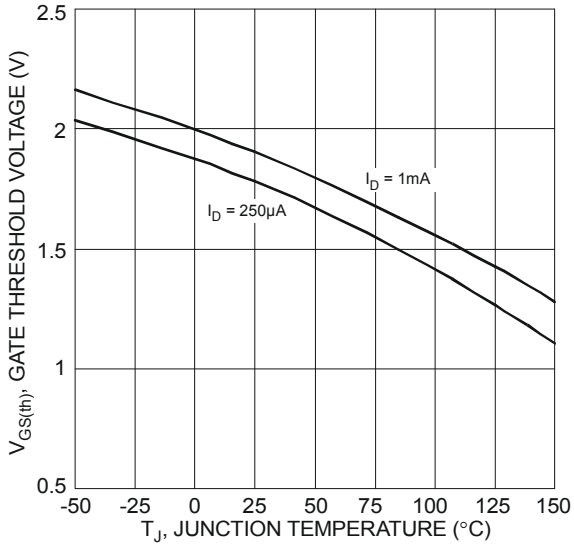


Figure 7 Gate Threshold Variation vs. Ambient Temperature

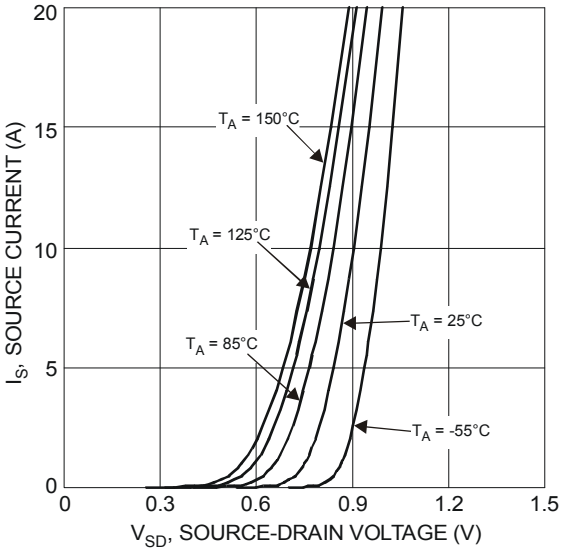


Figure 8 Diode Forward Voltage vs. Current

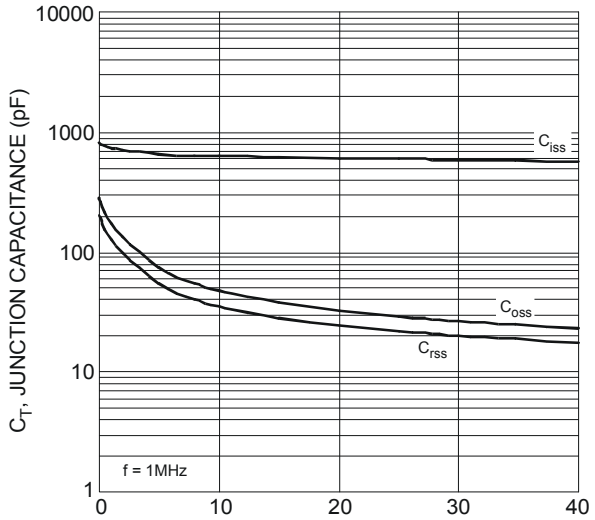


Figure 9 Typical Junction Capacitance

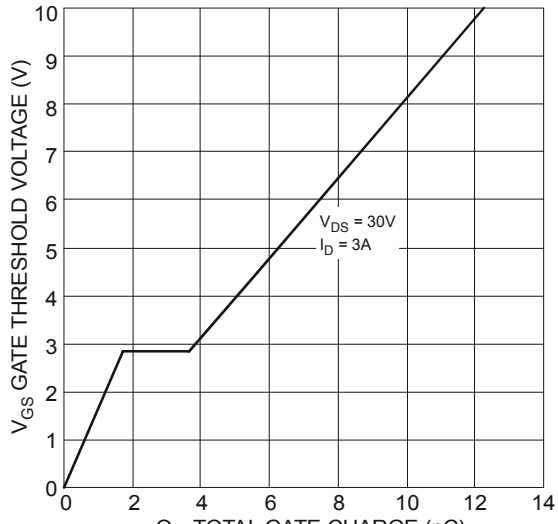
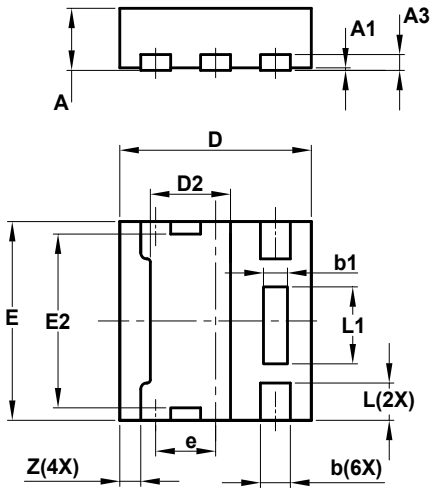


Figure 10 Gate Charge

Package Outline Dimensions

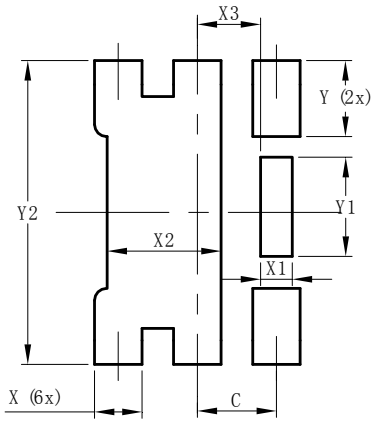
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



X1-DFN1616-6 Type E			
Dim	**Min**	**Max**	**Typ**
A	0.47	0.53	0.50
A1	0	0.05	0.02
A3	—	—	0.13
b	0.20	0.30	0.25
b1	0.10	0.30	0.20
D	1.55	1.65	1.60
D2	0.57	0.77	0.67
E	1.55	1.65	1.60
E2	1.30	1.50	1.40
e	—	—	0.50
L	0.25	0.35	0.30
L1	0.52	0.72	0.62
Z	—	—	0.175
All Dimensions in mm			

Suggested Pad Layout

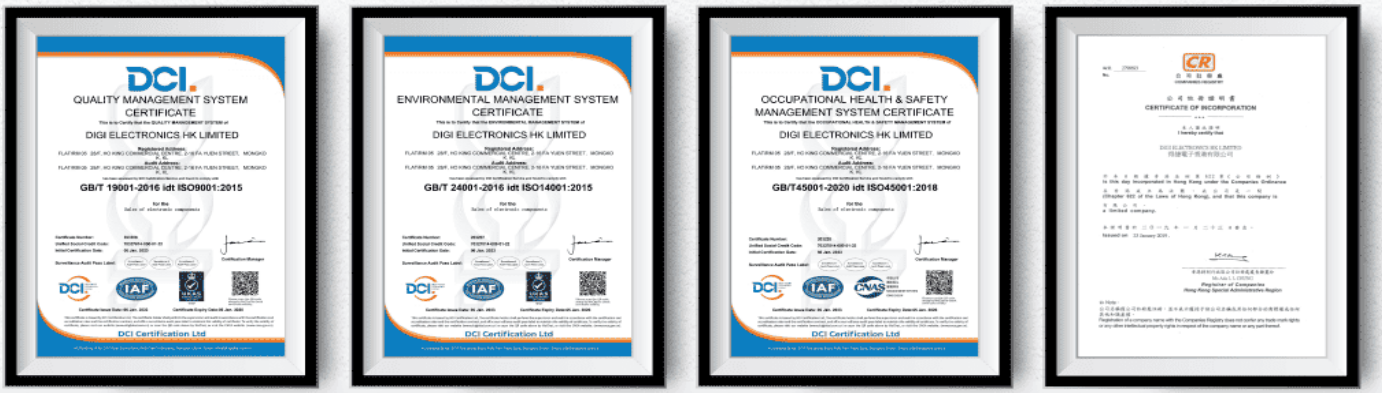
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
C	0.500
X	0.300
X1	0.200
X2	0.720
X3	0.400
Y	0.475
Y1	0.620
Y2	1.900

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.